

NPN Multi-Chip General-Purpose Amplifier FMB3904, MMPQ3904

Description

This device is designed as a general-purpose amplifier and switch. The useful dynamic range extends to 100 mA as a switch and to 100 MHz as an amplifier. Sourced from Process 23.

ABSOLUTE MAXIMUM RATINGS (Note 1)

Symbol	Parameter	Value	Unit
V_{CEO}	Collector-Emitter Voltage	40	V
V_{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	6.0	V
Ic	Collector Current - Continuous	200	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

 These ratings are based on a maximum junction temperature of 150°C. These are steady-state limits. onsemi should be consulted on applications involving pulsed or low-duty cycle operations.

THERMAL CHARACTERISTICS (Note 2)

(Values are at T_A = 25°C, unless otherwise noted.)

		Max		
Symbol	Parameter	FMB3904	MMPQ3904	Unit
P _D	Total Device Dissipation	700	1,000	mW
	Derate Above 25°C	5.6	8.0	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	180	-	°C/W
	Thermal Resistance, Junction to Ambient, Effective 4 Die	-	125	
	Thermal Resistance, Junction to Ambient, Each Die	-	240	

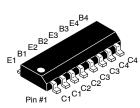
 PCB size: FR-4 76 x 114 x 0.6T mm³ (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

MARKING DIAGRAM





TSOT23 6-Lead CASE 419BL





SOIC-16 CASE 751BG

1A, MMPQ3904 = Specific Device Code

M = Date Code

■ Pb-Free Package

A = Assembly Site

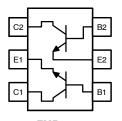
WL = Wafer Lot Number

Y = Year of Production

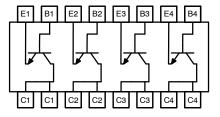
WW = Work Week Number

(Note: Microdot may be in either location)

INTERNAL CONNECTIONS



FMB3904



MMPQ3904

ORDERING INFORMATION

Device	Package	Shipping [†]
FMB3904	TSOT23 (Pb-Free, Halide Free)	3000 / Tape & Reel
MMPQ3904	SOIC-16 (Pb-Free, Halide Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (Values are at T_A = 25°C unless otherwise noted.)

Symbol	Parameter		Conditions	Min	Тур	Max	Unit
OFF CHAR	ACTERISTICS					•	•
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage		I _C = 1.0 mA, I _B = 0	40	_	_	V
V _{(BR)CBO}	Collector-Base Breakdown \	oltage/	$I_C = 10 \mu A, I_E = 0$	60	-	-	V
V _{(BR)EBO}	Emitter-Base Breakdown Vo	Itage	$I_E = 10 \mu A, I_C = 0$	6.0	-	-	V
I _{BL}	Base Cut-Off Current Collector Cut-Off Current		V _{CE} = 30 V, V _{BE} = -3 V	_	-	50	nA
I _{CEX}			V _{CE} = 30 V, V _{BE} = -3 V	_	-	50	nA
ON CHARA	CTERISTICS (Note 3)						
h _{FE}	DC Current Gain	FMB3904	I _C = 0.1 mA, V _{CE} = 1.0 V	40	_	_	
		MMPQ3904		30	_	-	
		FMB3904	I _C = 1.0 mA, V _{CE} = 1.0 V	70	_	-	
		MMPQ3904		50	_	-	
		FMB3904	I _C = 10 mA, V _{CE} = 1.0 V	100	_	300	
		MMPQ3904		75	-	-	
		All Devices	I _C = 50 mA, V _{CE} = 1.0 V	60	_	-	
		All Devices	I _C = 100 mA, V _{CE} = 1.0 V	30	_	-	
V _{CE} (sat)	Collector-Emitter Saturation Voltage		I _C = 10 mA, I _B = 1.0 mA	_	_	0.2	V
			I _C = 50 mA, I _B = 5.0 mA	_	_	0.3	
V _{BE} (sat)	Base-Emitter Saturation Voltage		I _C = 10 mA, I _B = 1.0 mA	0.65	_	0.85	V
			I _C = 50 mA, I _B = 5.0 mA	_	_	0.95	
MALL-SIG	NAL CHARACTERISTICS (MI	MPQ3904 ONLY)					
f _T	Current Gain-Bandwidth Product		I _C = 10 mA, V _{CE} = 20 V, f = 100 MHz	-	200	-	MHz
C _{ob}	Output Capacitance		V _{CB} = 5.0 V, I _E = 0, f = 140 kHz	_	4.0	-	pF
C _{ib}	Input Capacitance		V _{EB} = 0.5 V, I _C = 0, f = 140 kHz	_	8.0	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse test: pulse width $\leq 300 \ \mu s$, duty cycle $\leq 2.0\%$.

TYPICAL PERFORMANCE CHARACTERISTICS

V_{BE(ON)}, BASE EMITTER ON VOLTAGE (V)

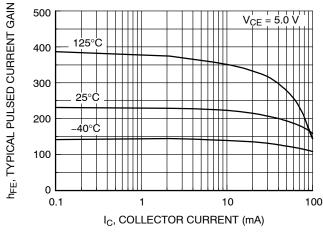


Figure 1. Typical Pulsed Current Gain vs. Collector Current

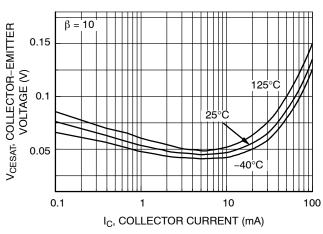


Figure 2. Collector-Emitter Saturation Voltage vs. Collector Current

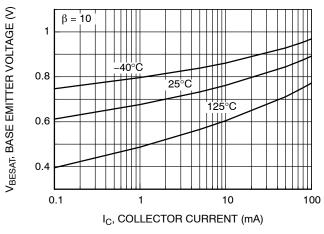


Figure 3. Base-Emitter Saturation Voltage vs.
Collector Current

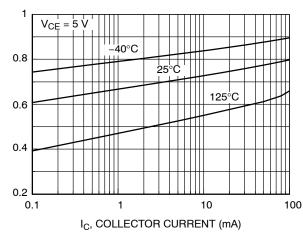


Figure 4. Base-Emitter On Voltage vs. Collector Current

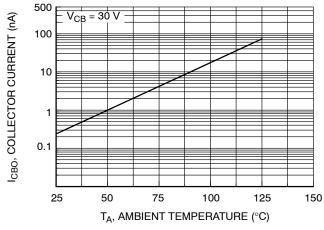


Figure 5. Collector Cut-Off Current vs.
Ambient Temperature

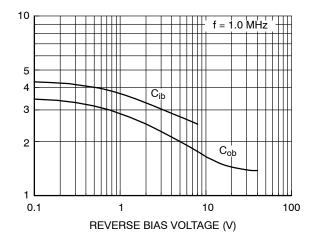


Figure 6. Capacitance vs. Reverse Bias Voltage

CAPACITANCE (pF)

TYPICAL PERFORMANCE CHARACTERISTICS (CONTINUED)

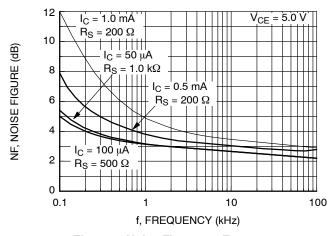


Figure 7. Noise Figure vs. Frequency

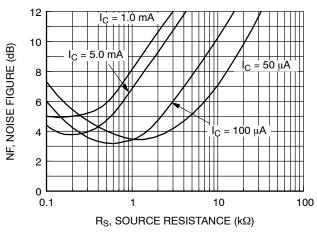


Figure 8. Noise Figure vs. Source Resistance

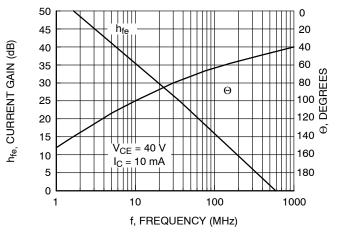


Figure 9. Current Gain and Phase Angle vs. Frequency

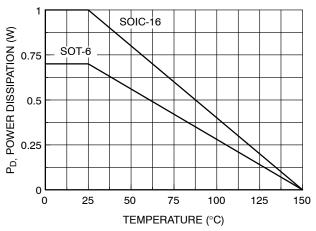


Figure 10. Power Dissipation vs.
Ambient Temperature

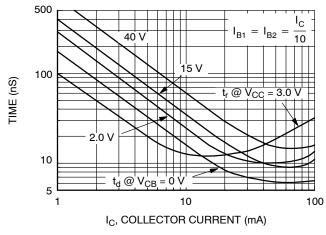


Figure 11. Turn-On Time vs. Collector Current

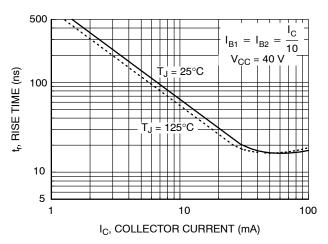


Figure 12. Rise Time vs. Collector Current

TYPICAL PERFORMANCE CHARACTERISTICS (CONTINUED)

h_{oe}, OUTPUT ADMITTANCE (μmhos)

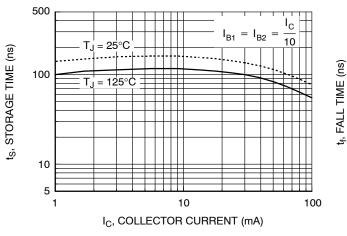


Figure 13. Storage Time vs. Collector Current

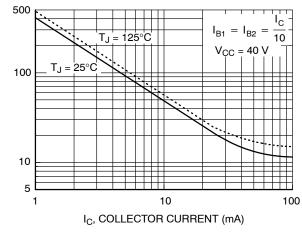


Figure 14. Fall Time vs. Collector Current

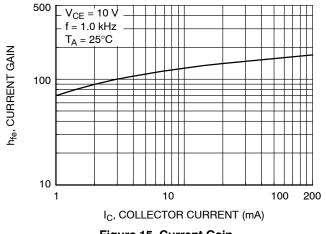


Figure 15. Current Gain

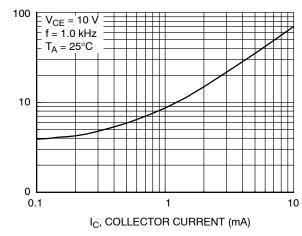


Figure 16. Output Admittance

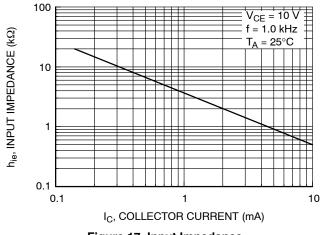


Figure 17. Input Impedance

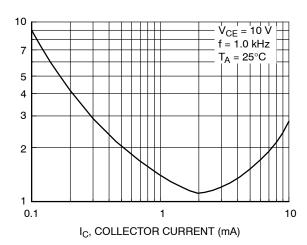


Figure 18. Voltage Feedback Ratio

h_{re}, VOLTAGE FEEDBACK RATIO (x10⁻⁴)



0.20 C



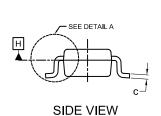
PIN 1 **IDENTIFIER**

TSOT23 6-Lead CASE 419BL **ISSUE A**

DATE 31 AUG 2020

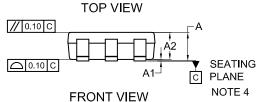
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- CONTROLLING DIMENSION: MILLIMETERS
 DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,
 PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.25MM PER END. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
- 4. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



	MIN.	NOM.	MAX.
Α	0.90	1.00	1.10
A1	0.00	0.05	0.10
A2	0.70	0.85	1.00
А3		0.25 BSC	
b	0.25	0.38	0.50
С	0.10	0.18	0.26
D	2.80	2.95	3.10
d	0.30 REF		
Е	2.50	2.75	3.00
E1	1.30	1.50	1.70
е	0.95 BSC		
e1	1.90 BSC		
L1	0.60 REF		
L2	0.20	0.40	0.60
Д	U _o		10°

MILLIMETERS



e1

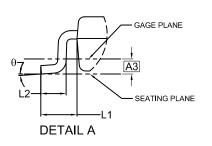
A

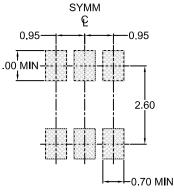
E1

-b

В

0.20 C





LAND PATTERN RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.





XXX = Specific Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " • ", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	TSOT23 6-Lead		PAGE 1 OF 1

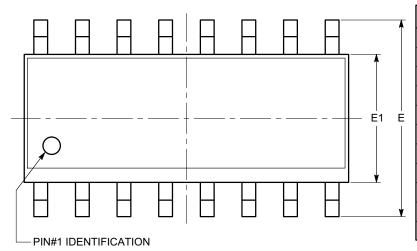
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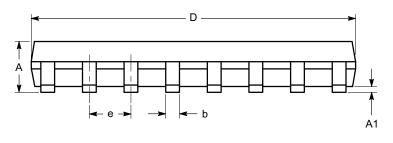
SOIC-16, 150 mils CASE 751BG ISSUE O

DATE 19 DEC 2008

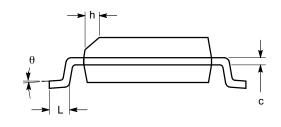


SYMBOL	MIN	NOM	MAX
Α	1.35		1.75
A1	0.10		0.25
b	0.33		0.51
С	0.19		0.25
D	9.80	9.90	10.00
Е	5.80	6.00	6.20
E1	3.80	3.90	4.00
е		1.27 BSC	
h	0.25		0.50
L	0.40		1.27
θ	0°		8°

TOP VIEW



SIDE VIEW



END VIEW

Notes:

- (1) All dimensions are in millimeters. Angles in degrees.
- (2) Complies with JEDEC MS-012.

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